

BC807-25 BC807-40

SMALL SIGNAL PNP TRANSISTORS

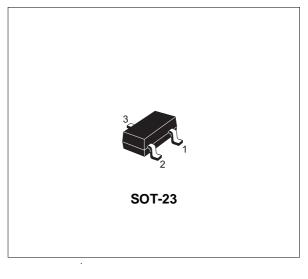
PRELIMINARY DATA

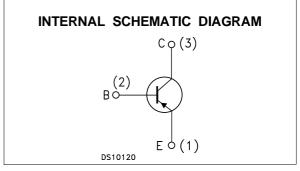
Туре	Marking
BC807-25	5B
BC807-40	5C

- SILICON EPITAXIAL PLANAR PNP TRANSISTORS
- MINIATURE SOT-23 PLASTIC PACKAGE FOR SURFACE MOUNTING CIRCUITS
- TAPE AND REEL PACKING
- THE NPN COMPLEMENTARY TYPES ARE BC817-25 AND BC817-40 RESPECTIVELY

APPLICATIONS

- WELL SUITABLE FOR PORTABLE EQUIPMENT
- SMALL LOAD SWITCH TRANSISTORS WITH HIGH GAIN AND LOW SATURATION VOLTAGE





ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage $(I_E = 0)$	-50	V
Vceo	Collector-Emitter Voltage (I _B = 0)	-45	V
V _{EBO}	Emitter-Base Voltage ($I_c = 0$)	-5	V
lc	Collector Current	-0.5	А
I _{CM}	Collector Peak Current	-1	А
P _{tot}	Total Dissipation at T_{C} = 25 $^{\circ}C$	250	mW
T _{stg}	Storage Temperature	nperature -65 to 150	
Tj	Max. Operating Junction Temperature	150	°C

THERMAL DATA

R _{thj-amb} •	Thermal Resistance Junction-Ambient	Max	500	°C/W
Device mour	nted on a PCB area of 1 cm ²			

ELECTRICAL CHARACTERISTICS ($T_{case} = 25 \ ^{\circ}C$ unless otherwise specified)

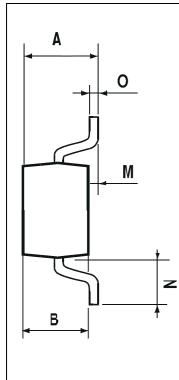
Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
I _{CBO}	Collector Cut-off Current (I _E = 0)	$V_{CB} = -20 V$ $V_{CB} = -20 V$ $T_{C} = 150^{\circ}C$			-100 -5	nΑ μΑ
I _{EBO}	Emitter Cut-off Current $(I_C = 0)$	V _{EB} = -5 V			-100	nA
$V_{(BR)CEO^*}$	Collector-Emitter Breakdown Voltage (I _B = 0)	I _C = -10 mA	-45			V
V _{CE(sat)} *	Collector-Emitter Saturation Voltage	$I_{\rm C} = -500 \text{ mA}$ $I_{\rm B} = -50 \text{ mA}$			-0.7	V
$V_{BE(on)}*$	Base-Emitter On Voltage	$I_{C} = -500 \text{ mA}$ $V_{CE} = -1 \text{ V}$			-1.2	V
h _{FE} *	DC Current Gain	Ic = -100 mA V _{CE} = -1 V for BC807-25 for BC807-40	160 250		400 600	
f⊤	Transition Frequency	I_{C} = -10 mA V_{CE} = -5 V f =100 MHz	80			MHz
Ссво	Collector-Base Capacitance	$I_E = 0 \qquad V_{CB} = -10 \text{ V} \qquad f = 1 \text{ MHz}$		9		рF

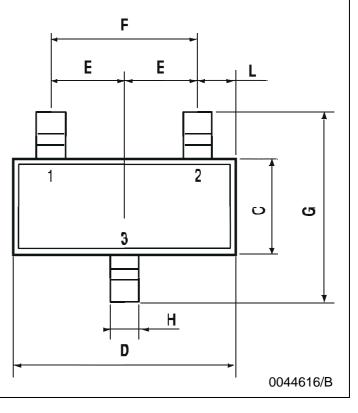
* Pulsed: Pulse duration = 300 $\mu s,$ duty cycle \leq 2 %

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DIM.	mm			mils		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
А	0.85		1.1	33.4		43.3
В	0.65		0.95	25.6		37.4
С	1.20		1.4	47.2		55.1
D	2.80		3	110.2		118
E	0.95		1.05	37.4		41.3
F	1.9		2.05	74.8		80.7
G	2.1		2.5	82.6		98.4
н	0.38		0.48	14.9		18.8
L	0.3		0.6	11.8		23.6
М	0		0.1	0		3.9
N	0.3		0.65	11.8		25.6
0	0.09		0.17	3.5		6.7

SOT-23 MECHANICAL DATA





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